

FDS6930B

Dual N-Channel Logic Level PowerTrench® MOSFET

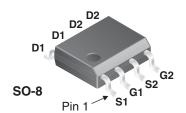
Features

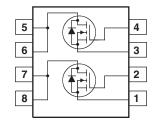
- 5.5 A, 30 V. $R_{DS(ON)} = 38 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$ $R_{DS(ON)} = 50 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low R_{DS(ON)}
- High power and current handling capability

General Description

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.





Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage	30	V	
V _{GSS}	Gate-Source Voltage		± 20	V
I _D	Drain Current - Continuous	(Note 1a)	5.5	А
	- Pulsed		20	
P _D	Power Dissipation for Dual Operation	(Note 1)	2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to 150	°C
Thermal Cha	racteristics			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6930B	FDS6930B	13"	12mm	2500 units

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charac	teristics	•	•		,	•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		26		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			1 10	μА
I _{GSS}	Gate-Source Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Charact	teristics (Note 2)		•	•	,	•
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		-4.6		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 4.8 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}, T_J = 125^{\circ}\text{C}$		31 40 45	38 50 62	mΩ
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	20			Α
9 _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 5.5 A		19		S
Dynamic C	haracteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		310	412	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		90	120	pF
C _{rss}	Reverse Transfer Capacitance			40	60	pF
R _G	Gate Resistance	V _{GS} = 15 mV, f = 1.0 MHz		1.9		Ω
Switching (Characteristics (Note 2)		'			
t _{d(on)}	Turn-On Delay Time	V _{DD} = 15 V, I _D = 1 A,		6	12	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_{GEN} = 6 Ω		6	12	ns
t _{d(off)}	Turn-Off Delay Time			16	28	ns
t _f	Turn-Off Fall Time			2	4	ns
Q _q	Total Gate Charge	V _{DS} = 15 V, I _D = 5.5 A,		2.7	3.8	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 5 V$		1.0		nC
Q _{gd}	Gate-Drain Charge			0.7		nC
	rce Diode Characteristics and Maximun	n Ratings		l .		I
I _S	Maximum Continuous Drain-Source Did	ode Forward Current			1.3	А
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.3 A (Note 2)		0.8	1.2	V
t _{rr}	Diode Reverse Recovery Time (note3)	$I_F = 5.5 \text{ A}, d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$		16	32	nS
Q _{rr}	Diode Reverse Recovery Charge			6		nC

Notes

R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in² pad of 2 oz



b) 125°C/W when mounted on a 0.02 in² pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.

Scale 1:1 on letter size paper

- 2. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%
- 3. Trr parameter will not be subjected to 100% production testing.

Typical Characteristics

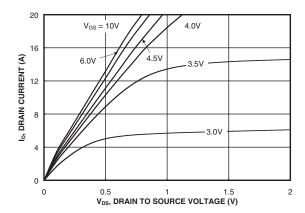


Figure 1. On-Region Characteristics.

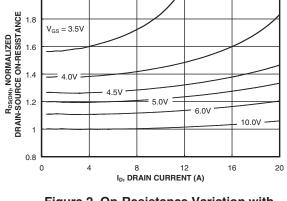


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

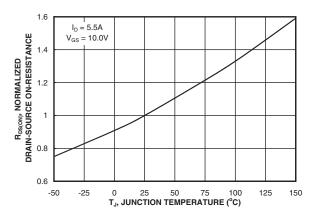


Figure 3. On-Resistance Variation with Temperature.

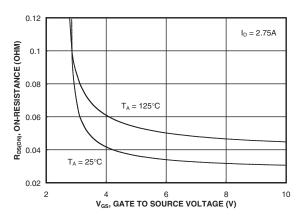


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

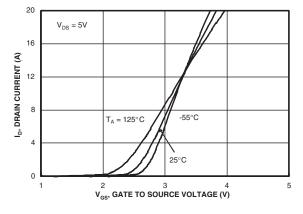


Figure 5. Transfer Characteristics.

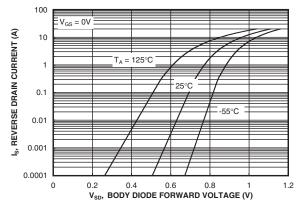
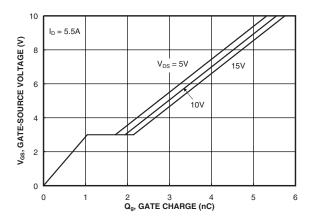


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

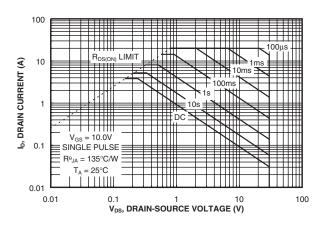
Typical Characteristics



 $\begin{array}{c} \textbf{500} \\ \textbf{400} \\ \textbf{400} \\ \textbf{400} \\ \textbf{200} \\ \textbf{C}_{\text{GS}} \\ \textbf{C}_{\text{OSS}} \\ \textbf{C}_{\text{OSS}} \\ \textbf{V}_{\text{DS}}, \textbf{DRAIN TO SOURCE VOLTAGE}(\textbf{V}) \\ \end{array}$

Figure 7. Gate Charge Characteristics.





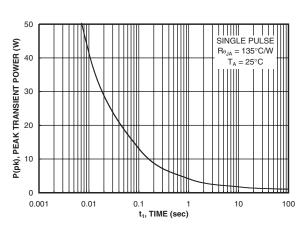


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

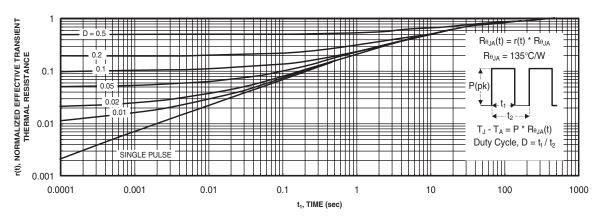


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





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